

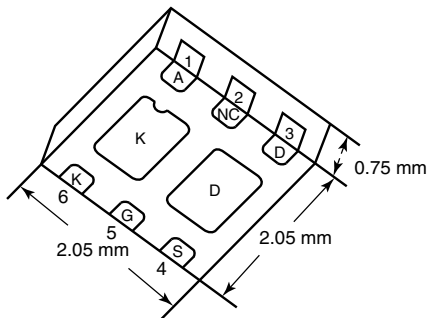


## P-Channel 30 V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) Max.	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)
- 30	0.065 at V <sub>GS</sub> = - 10 V	- 4.5 <sup>a</sup>	6.6 nC
	0.080 at V <sub>GS</sub> = - 4.5 V	- 4.5 <sup>a</sup>	
	0.092 at V <sub>GS</sub> = - 3.7 V	- 4.5 <sup>a</sup>	
	0.125 at V <sub>GS</sub> = - 2.5 V	- 3	

SCHOTTKY PRODUCT SUMMARY		
V <sub>KA</sub> (V)	V <sub>f</sub> (V) Diode Forward Voltage	I <sub>F</sub> (A) <sup>a</sup>
30	0.56 at 1 A	2

PowerPAK SC-70-6 Dual



Ordering Information:  
SiA817EDJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

### FEATURES

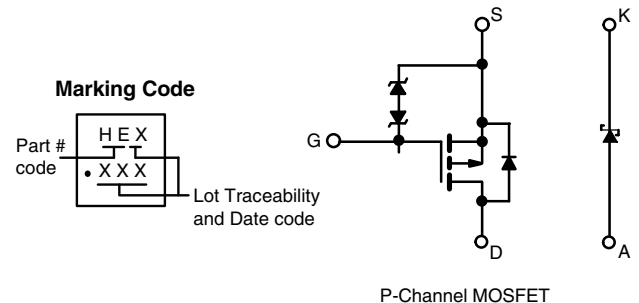
- LITTLE FOOT® Plus Schottky Power MOSFET
- Thermally Enhanced PowerPAK® SC-70 Package
  - Small Footprint Area
  - Low On-Resistance
  - Thin 0.75 mm Profile
- Typical ESD Protection (MOSFET): 1500 V (HBM)
- 100 % R<sub>g</sub> Tested
- Material categorization: For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



RoHS  
COMPLIANT  
HALOGEN  
FREE

### APPLICATIONS

- Portable Devices such as Smart Phones, Tablet PCs and Mobile Computing
  - Battery Charger Switch
  - Buck Converter
  - Power Management



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage (MOSFET)	V <sub>DS</sub>	- 30	V
Reverse Voltage (Schottky)	V <sub>KA</sub>	30	
Gate-Source Voltage (MOSFET)	V <sub>GS</sub>	± 12	
Continuous Drain Current (T <sub>J</sub> = 150 °C) (MOSFET)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	- 4.5 <sup>a</sup>
		T <sub>C</sub> = 70 °C	- 4.5 <sup>a</sup>
		T <sub>A</sub> = 25 °C	- 4.2 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	- 3.4 <sup>b, c</sup>
Pulsed Drain Current (MOSFET) (t = 300 μs)	I <sub>DM</sub>	- 15	A
Continuous Source-Drain Diode Current (MOSFET Diode Conduction)	I <sub>S</sub>	T <sub>C</sub> = 25 °C	
		T <sub>A</sub> = 25 °C	- 1.6 <sup>b, c</sup>
Average Forward Current (Schottky)	I <sub>F</sub>	2 <sup>b</sup>	A
Pulsed Forward Current (Schottky)	I <sub>FM</sub>	3	
Maximum Power Dissipation (MOSFET)	P <sub>D</sub>	T <sub>C</sub> = 25 °C	6.5
		T <sub>C</sub> = 70 °C	5
		T <sub>A</sub> = 25 °C	1.9 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	1.2 <sup>b, c</sup>
Maximum Power Dissipation (Schottky)	P <sub>D</sub>	T <sub>C</sub> = 25 °C	6.8
		T <sub>C</sub> = 70 °C	4.3
		T <sub>A</sub> = 25 °C	1.6 <sup>b, c</sup>
		T <sub>A</sub> = 70 °C	1 <sup>b, c</sup>
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) <sup>d, e</sup>		260	

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient (MOSFET) <sup>b, f</sup>	$t \leq 5 \text{ s}$	$R_{thJA}$	52	65	°C/W
Maximum Junction-to-Case (Drain) (MOSFET)	Steady State	$R_{thJC}$	12.5	16	
Maximum Junction-to-Ambient (Schottky) <sup>b, f</sup>	$t \leq 5 \text{ s}$	$R_{thJA}$	62	76	
Maximum Junction-to-Case (Drain) (Schottky)	Steady State	$R_{thJC}$	15	18.5	

## Notes:

- Package limited.
- Surface mounted on 1" x 1" FR4 board.
- $t = 10 \text{ s}$ .
- See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 110 °C/W.

### SPECIFICATIONS ( $T_J = 25 \text{ }^\circ\text{C}$ , unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-30			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250 \mu\text{A}$		-23		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			2.7		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 \mu\text{A}$	-0.6		-1.3	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			$\pm 0.5$	$\mu\text{A}$
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			$\pm 10$	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$			-1	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \leq 5 \text{ V}, V_{GS} = -10 \text{ V}$	-8			A
		$V_{GS} = -10 \text{ V}, I_D = -3 \text{ A}$		0.054	0.065	$\Omega$
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = -4.5 \text{ V}, I_D = -2 \text{ A}$		0.065	0.080	
		$V_{GS} = -3.7 \text{ V}, I_D = -1 \text{ A}$		0.070	0.092	
		$V_{GS} = -2.5 \text{ V}, I_D = -1 \text{ A}$		0.095	0.125	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = -10 \text{ V}, I_D = -3 \text{ A}$		9		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		600		pF
Output Capacitance	$C_{oss}$			55		
Reverse Transfer Capacitance	$C_{rss}$			50		
Total Gate Charge	$Q_g$	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -4.2 \text{ A}$		14	23	nC
				6.6	10	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = -4.2 \text{ A}$		1.3		
Gate-Drain Charge	$Q_{gd}$			2		
Gate Resistance	$R_g$		$f = 1 \text{ MHz}$	1.1	5.5	11
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15 \text{ V}, R_L = 4.4 \Omega$ $I_D \cong -3.4 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$		20	40	ns
Rise Time	$t_r$			20	40	
Turn-Off Delay Time	$t_{d(off)}$			23	45	
Fall Time	$t_f$			10	20	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15 \text{ V}, R_L = 4.4 \Omega$ $I_D \cong -3.4 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$		10	20	
Rise Time	$t_r$			10	20	
Turn-Off Delay Time	$t_{d(off)}$			25	50	
Fall Time	$t_f$			7	15	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25 \text{ }^\circ\text{C}$			-4.5	A
Pulse Diode Forward Current	$I_{SM}$				-15	
Body Diode Voltage	$V_{SD}$	$I_S = -3.4 \text{ A}, V_{GS} = 0 \text{ V}$		-0.9	-1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = -3.4 \text{ A}, dI/dt = 100 \text{ A}/\mu\text{s}, T_J = 25 \text{ }^\circ\text{C}$		16	30	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			8	15	nC
Reverse Recovery Fall Time	$t_a$			9		ns
Reverse Recovery Rise Time	$t_b$			7		

## Notes:

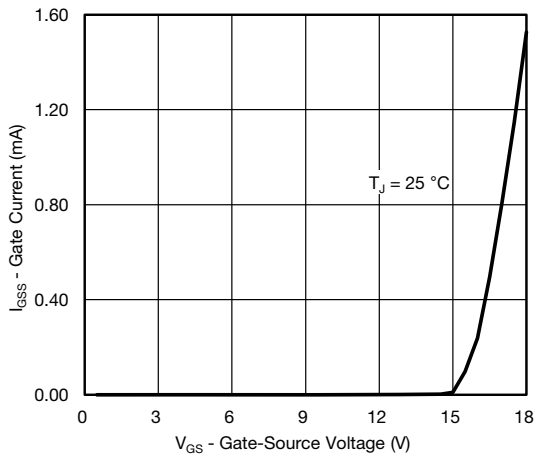
- Pulse test; pulse width  $\leq 300 \mu\text{s}$ , duty cycle  $\leq 2 \%$ .
- Guaranteed by design, not subject to production testing.



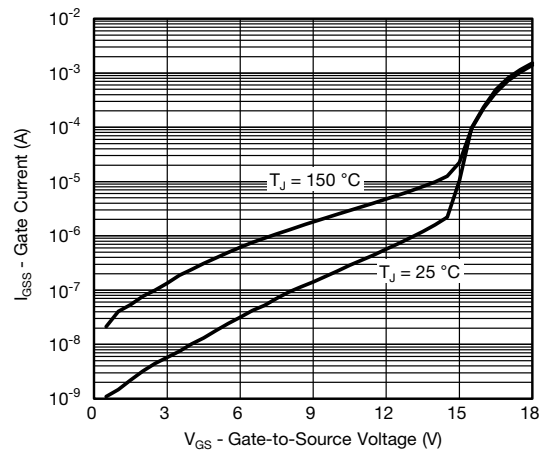
<b>SCHOTTKY SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Forward Voltage Drop	$V_F$	$I_F = 0.5\text{ A}$		0.37	0.45	V
		$I_F = 0.5\text{ A}, T_J = 125\text{ }^\circ\text{C}$		0.31	0.37	
		$I_F = 1\text{ A}$		0.46	0.56	
		$I_F = 1\text{ A}, T_J = 125\text{ }^\circ\text{C}$		0.41	0.50	
Maximum Reverse Leakage Current	$I_{rm}$	$V_r = 30\text{ V}$		0.025	0.100	mA
		$V_r = 30\text{ V}, T_J = 85\text{ }^\circ\text{C}$		0.6	6	
Junction Capacitance	$C_T$	$V_r = 15\text{ V}$		35		pF

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

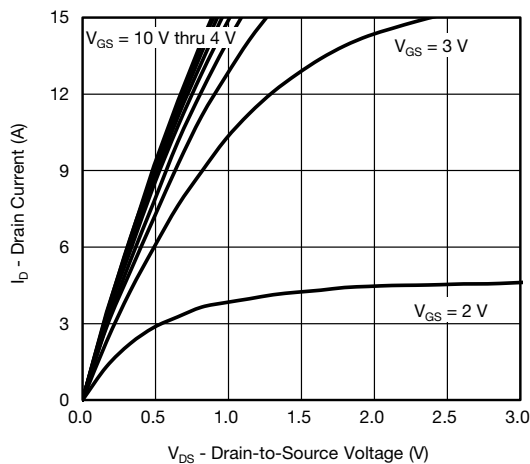
**MOSFET TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



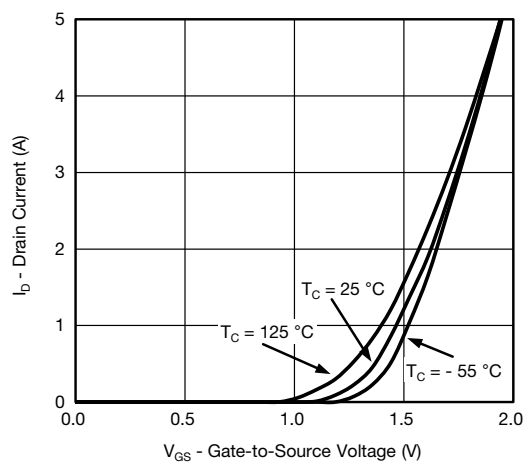
Gate-Source Voltage vs. Gate Current



Gate-Source Voltage vs. Gate Current



Output Characteristics



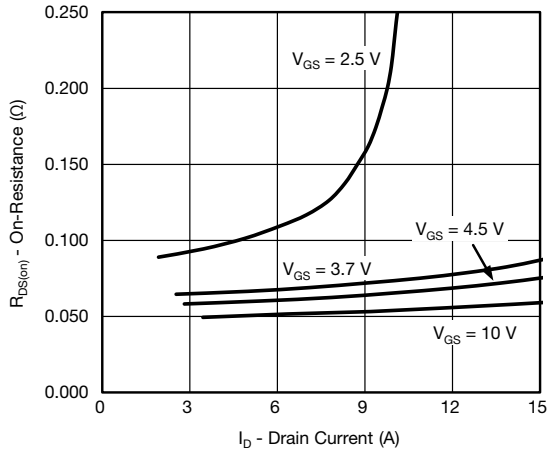
Transfer Characteristics

# SiA817EDJ

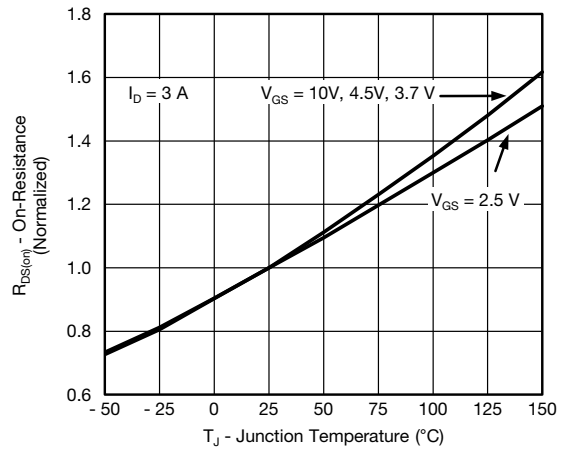
Vishay Siliconix



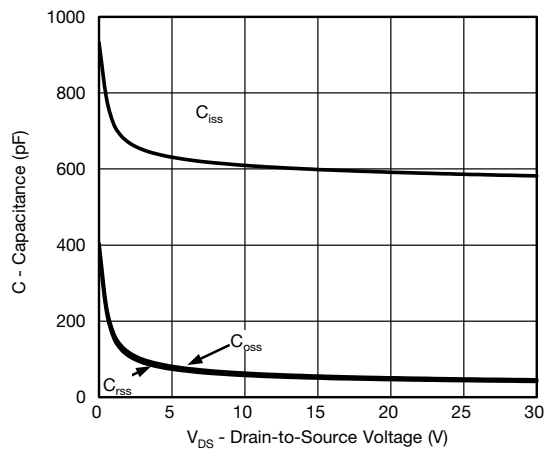
## MOSFET TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



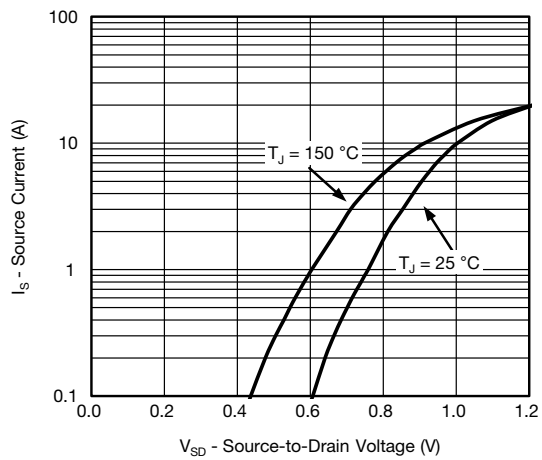
On-Resistance vs. Drain Current and Gate Voltage



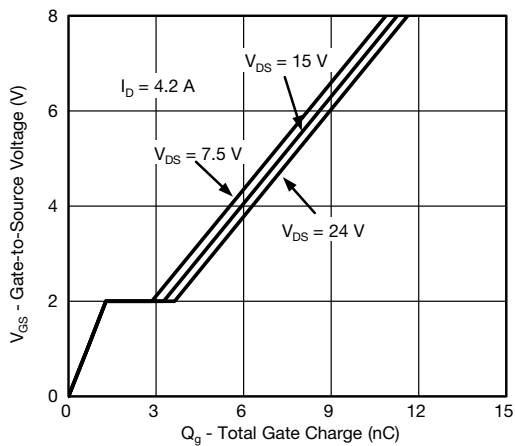
On-Resistance vs. Junction Temperature



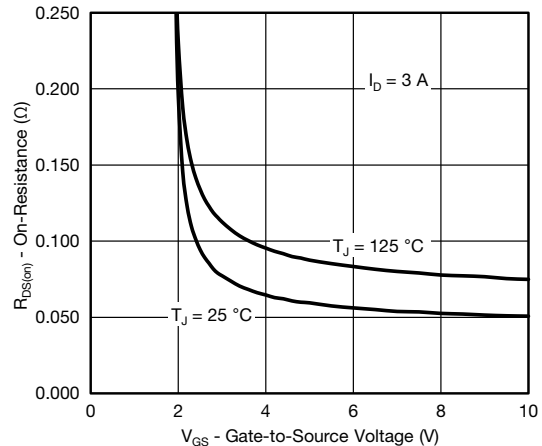
Capacitance



Source-Drain Diode Forward Voltage



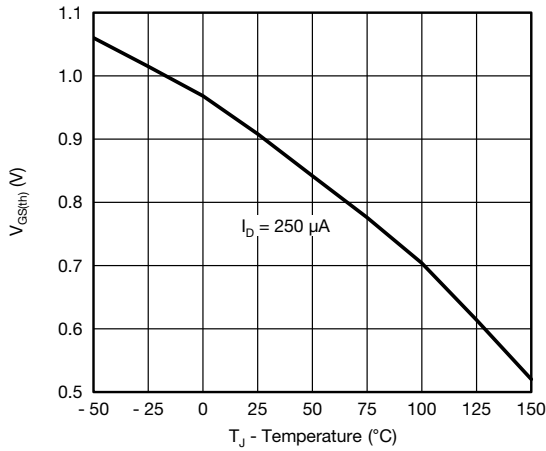
Gate Charge



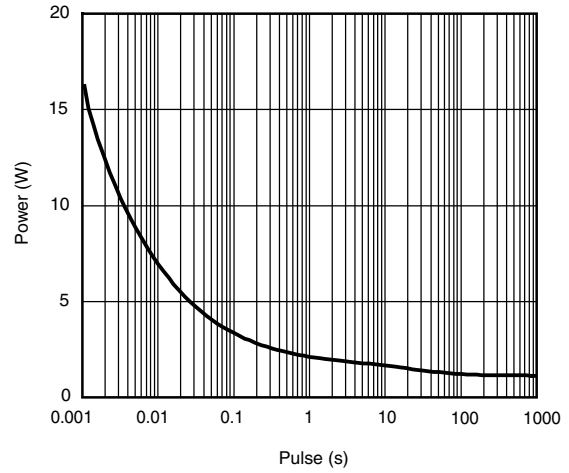
On-Resistance vs. Gate-to-Source Voltage



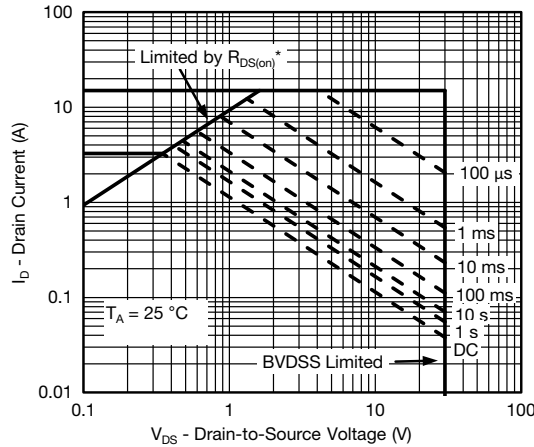
**MOSFET TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



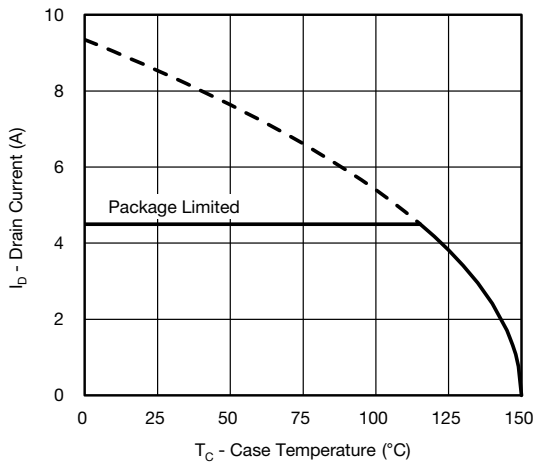
**Threshold Voltage**



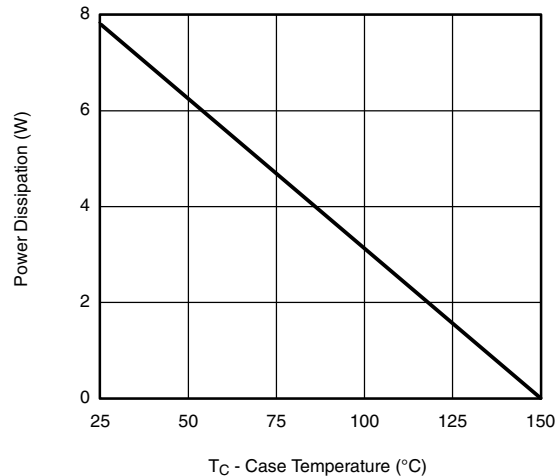
**Single Pulse Power, Junction-to-Ambient**



**Safe Operating Area, Junction-to-Case**



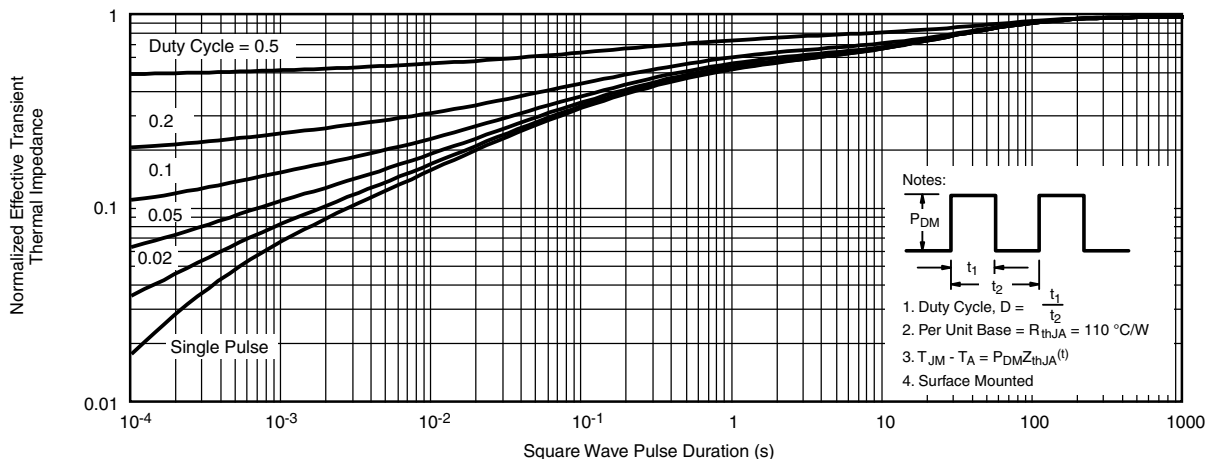
**Current Derating\***



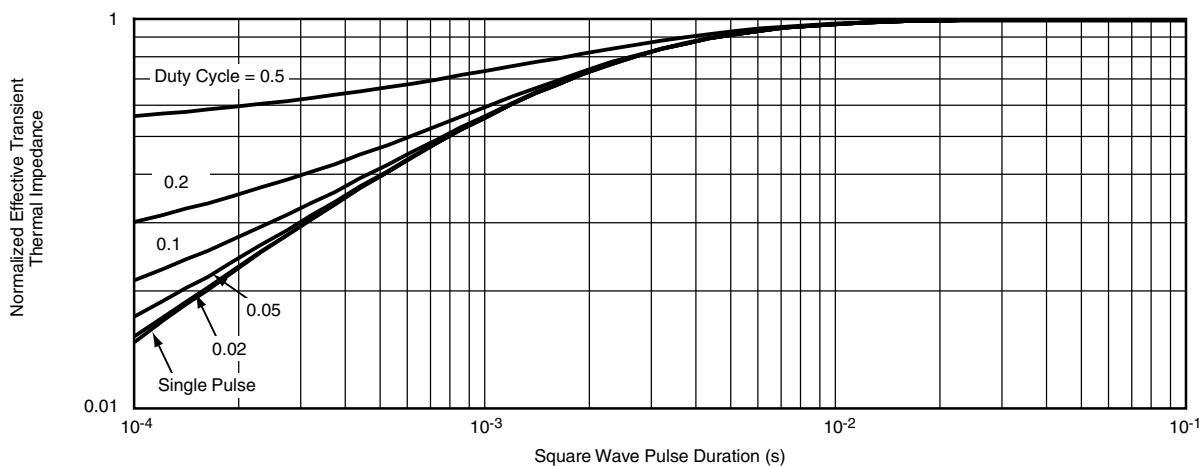
**Power Derating**

\* The power dissipation  $P_D$  is based on  $T_{J(max.)} = 150\text{ }^\circ\text{C}$ , using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**MOSFET TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



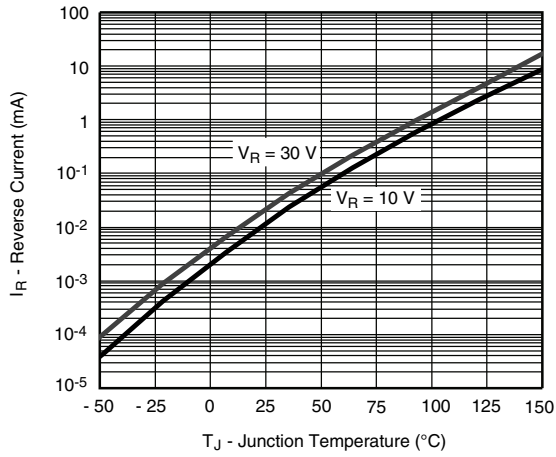
Normalized Thermal Transient Impedance, Junction-to-Ambient



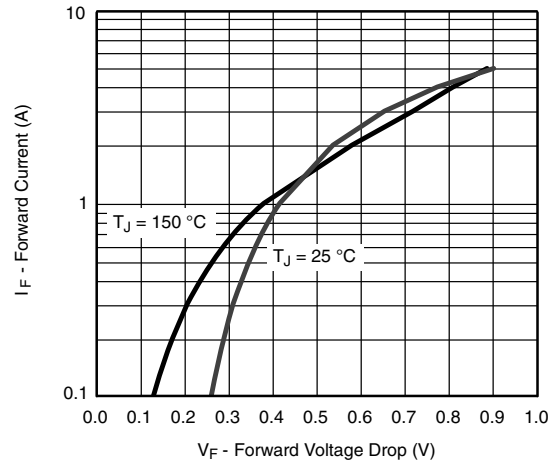
Normalized Thermal Transient Impedance, Junction-to-Case



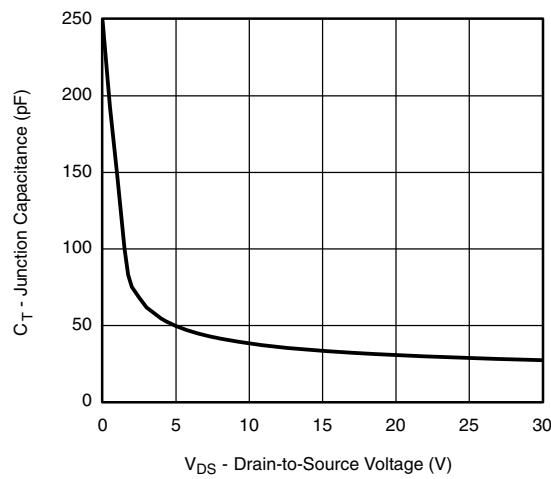
**SCHOTTKY TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



Reverse Current vs. Junction Temperature

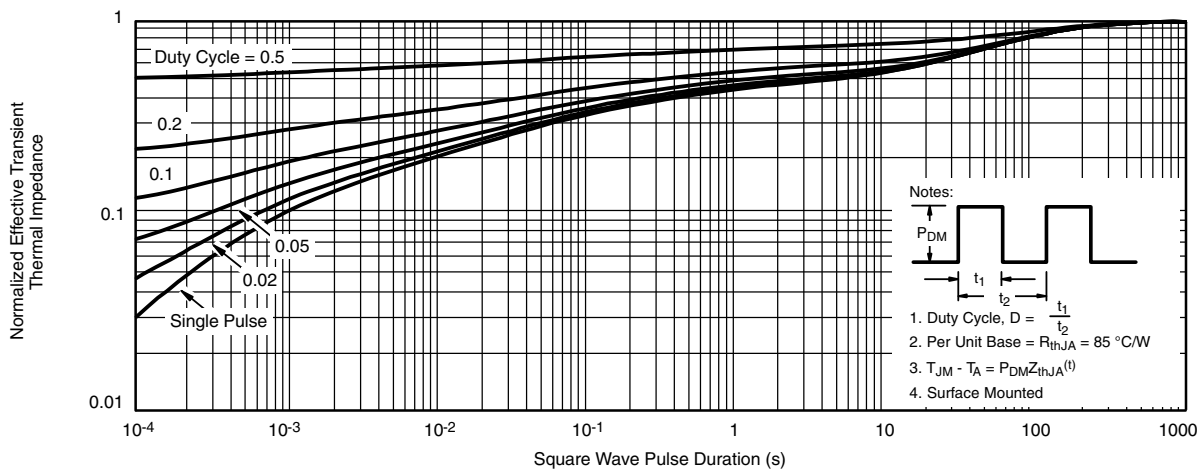


Forward Voltage Drop

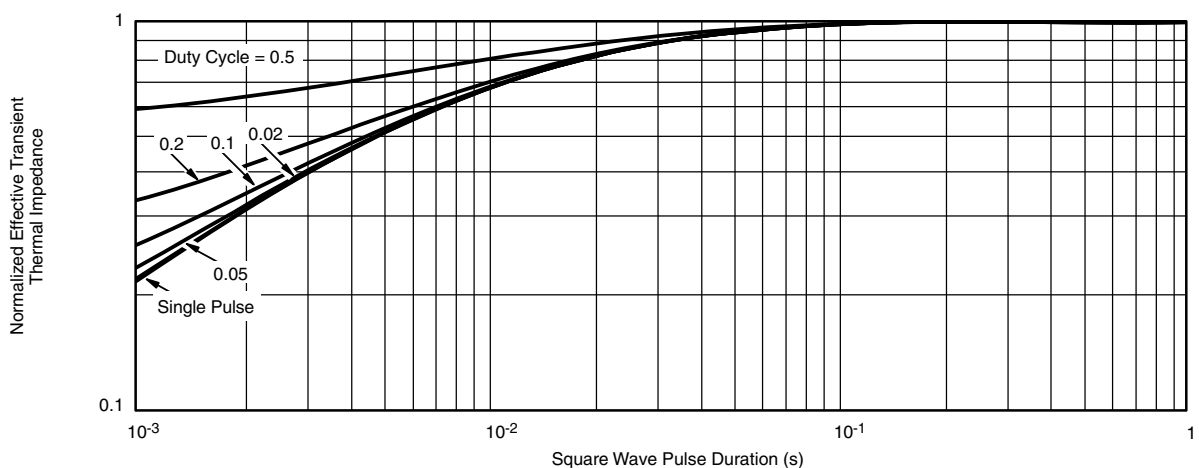


Capacitance

**SCHOTTKY TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



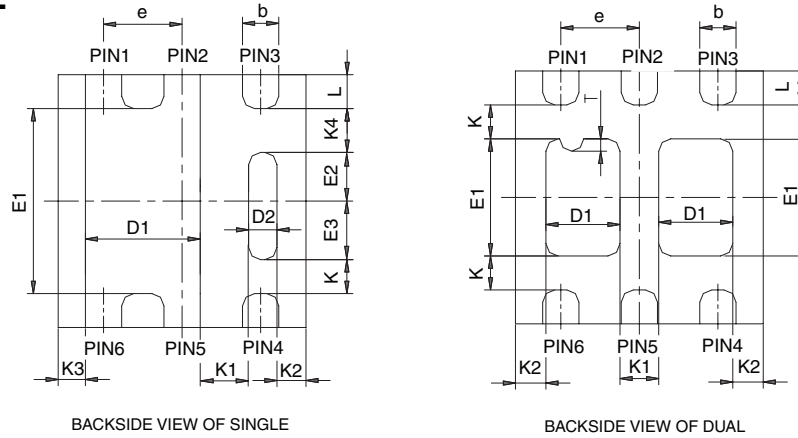
**Normalized Thermal Transient Impedance, Junction-to-Case**

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?62820](http://www.vishay.com/ppg?62820).



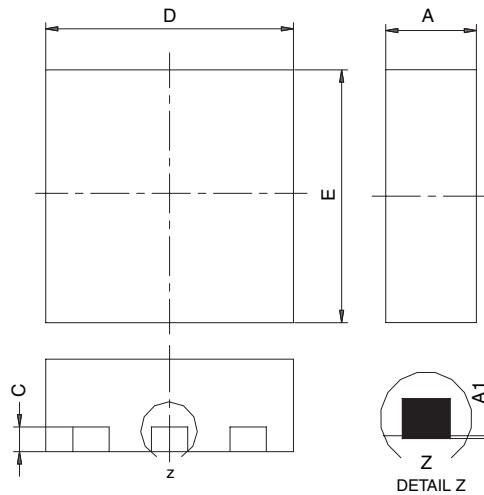


PowerPAK® SC70-6L



BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL

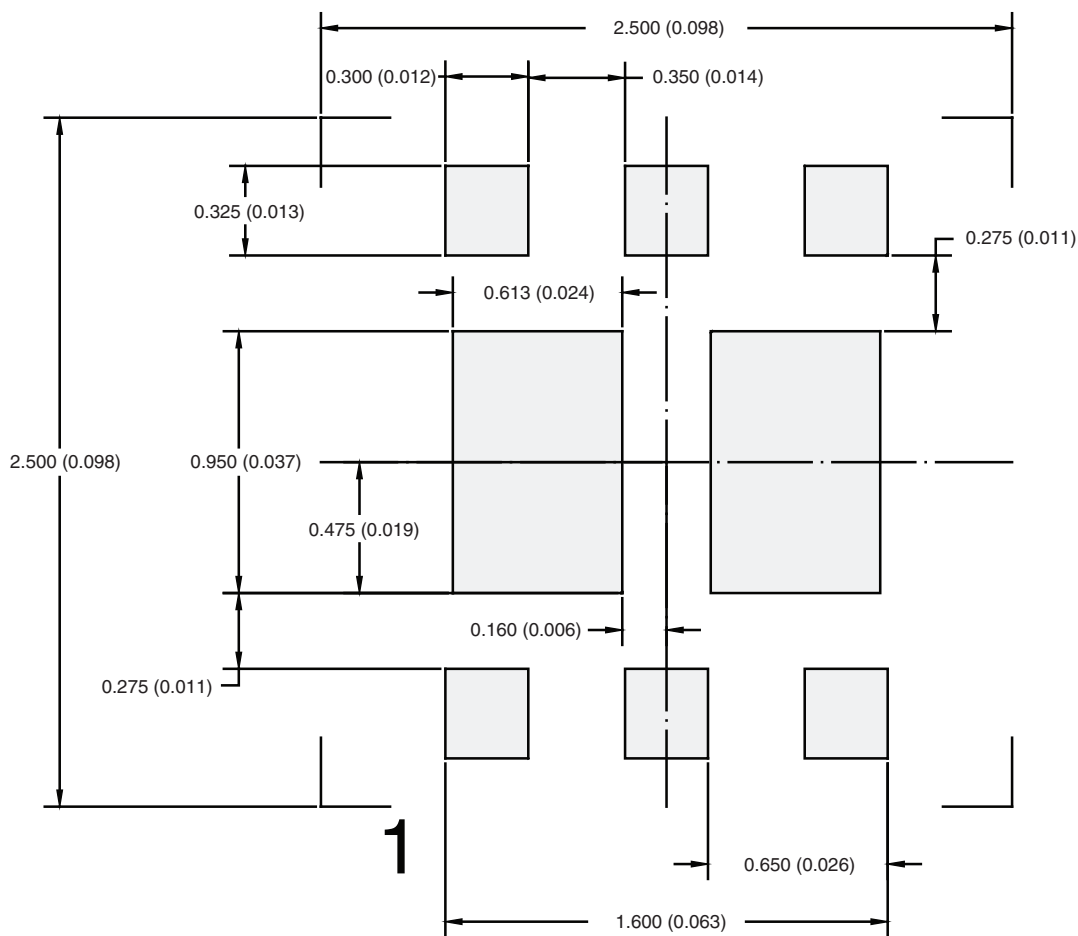


- Notes:  
 1. All dimensions are in millimeters  
 2. Package outline exclusive of mold flash and metal burr  
 3. Package outline inclusive of plating

DIM	SINGLE PAD						DUAL PAD					
	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
A	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
C	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
e	0.65 BSC			0.026 BSC			0.65 BSC			0.026 BSC		
K	0.275 TYP			0.011 TYP			0.275 TYP			0.011 TYP		
K1	0.400 TYP			0.016 TYP			0.320 TYP			0.013 TYP		
K2	0.240 TYP			0.009 TYP			0.252 TYP			0.010 TYP		
K3	0.225 TYP			0.009 TYP								
K4	0.355 TYP			0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
T							0.05	0.10	0.15	0.002	0.004	0.006

ECN: C-07431 – Rev. C, 06-Aug-07  
 DWG: 5934

## RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Dual



Dimensions in mm (inches)

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APPLICATION NOTE



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